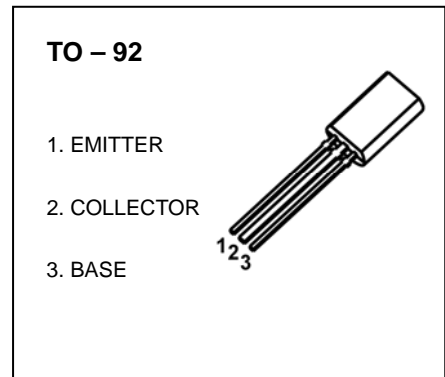
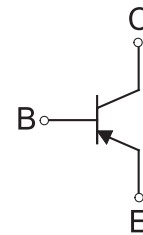


**FEATURES**

- Low Frequency Power Amplifier
- Complementary Pair with 2SD667


**MARKING**


B647=Device code  
 Solid dot = Green molding compound device,  
 if none, the normal device  
 XXX=Code

**Equivalent Circuit**

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-120	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-80	V
V <sub>EB0</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-1	A
P <sub>C</sub>	Collector Power Dissipation	750	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	167	°C/W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C

**ELECTRICAL CHARACTERISTICS**
 $T_a=25\text{ }^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-100\text{V}, I_E=0$			-10	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=-5\text{V}, I_C=-150\text{mA}$	60		320	
	$h_{FE(2)}$	$V_{CE}=-5\text{V}, I_C=-500\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=-5\text{V}, I_C=-150\text{mA}$			-1.5	V
Collector output capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		20		pF
Transition frequency	$f_T$	$V_{CE}=-5\text{V}, I_C=-150\text{mA}$		140		MHz

\*Pulse test

**CLASSIFICATION OF  $h_{FE(1)}$** 

RANK	B	C	D
RANGE	60-120	100-200	160-320

